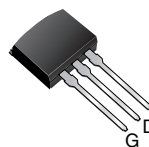
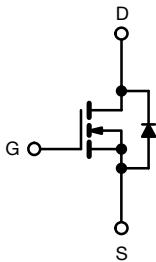


## Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.18
$Q_g$ max. (nC)	70	
$Q_{gs}$ (nC)	13	
$Q_{gd}$ (nC)	39	
Configuration	Single	

**I<sup>2</sup>PAK (TO-262)**

**D<sup>2</sup>PAK (TO-263)**


N-Channel MOSFET

### FEATURES

- Surface mount
- Low-profile through-hole
- Available in tape and reel
- Dynamic dV/dt rating
- 150 °C operating temperature
- Fast switching
- Fully avalanche rated
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.



**RoHS\***  
Available  
**HALOGEN**  
**FREE**  
Available

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combinations of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK is a surface mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the last lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application. The through-hole version (SiHF640L) is available for low-profile applications.

### ORDERING INFORMATION

Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)	I <sup>2</sup> PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHF640S-GE3	SiHF640STRL-GE3 <sup>a</sup>	SiHF640STRR-GE3 <sup>a</sup>	SiHF640L-GE3
Lead (Pb)-free	IRF640SPbF	IRF640STRLPbF <sup>a</sup>	IRF640STRRPbF <sup>a</sup>	-

#### Note

a. See device orientation.

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ °C}$ , unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	18	A
		11	A
Pulsed Drain Current <sup>a, e</sup>	$I_{DM}$	72	A
Linear Derating Factor		1.0	W/°C
Single Pulse Avalanche Energy <sup>b, e</sup>	$E_{AS}$	580	mJ
Avalanche Current <sup>a</sup>	$I_{AR}$	18	A
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	13	mJ
Maximum Power Dissipation	$P_D$	130	W
		3.1	W
Peak Diode Recovery dV/dt <sup>c, e</sup>	dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C
Soldering Recommendations (Peak temperature) <sup>d</sup>	for 10 s	300	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ °C}$ ,  $L = 2.7\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 18\text{ A}$  (see fig. 12).
- $I_{SD} \leq 18\text{ A}$ ,  $dI/dt \leq 150\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ °C}$ .
- 1.6 mm from case.
- Uses IRF640, SiHF640 data and test conditions.


**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB mounted, steady-state) <sup>a</sup>	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.0	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	200	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25^\circ\text{C}$ , $I_D = 1\text{ mA}$ <sup>c</sup>	-	0.29	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	25	$\mu\text{A}$
		$V_{DS} = 160\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 11\text{ A}$ <sup>b</sup>	-	-	0.18	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 11\text{ A}$ <sup>d</sup>	6.7	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5 <sup>d</sup>	-	1300	-	pF
Output Capacitance	$C_{oss}$		-	430	-	
Reverse Transfer Capacitance	$C_{rss}$		-	130	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$ , $I_D = 18\text{ A}$ , $V_{DS} = 160\text{ V}$ , see fig. 6 and 13 <sup>b, c</sup>	-	-	70	nC
Gate-Source Charge	$Q_{gs}$		-	-	13	
Gate-Drain Charge	$Q_{gd}$		-	-	39	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$ , $I_D = 18\text{ A}$ , $R_g = 9.1\text{ }\Omega$ , $R_D = 5.4\text{ }\Omega$ , see fig. 10 <sup>b, c</sup>	-	14	-	ns
Rise Time	$t_r$		-	51	-	
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	
Fall Time	$t_f$		-	36	-	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	0.5	-	3.6	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	18	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	72	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}$ , $I_S = 18\text{ A}$ , $V_{GS} = 0\text{ V}$ <sup>b</sup>	-	-	2.0	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}$ , $I_F = 18\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$ <sup>b, c</sup>	-	300	610	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	3.4	7.1	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .  
c. Uses IRF640/SiHF640 data and test conditions.



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

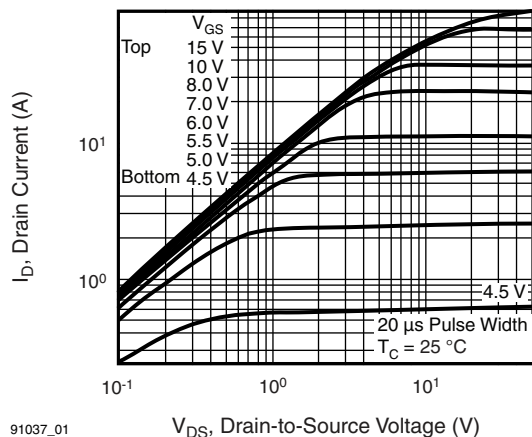


Fig. 1 - Typical Output Characteristics,  $T_J = 25$  °C

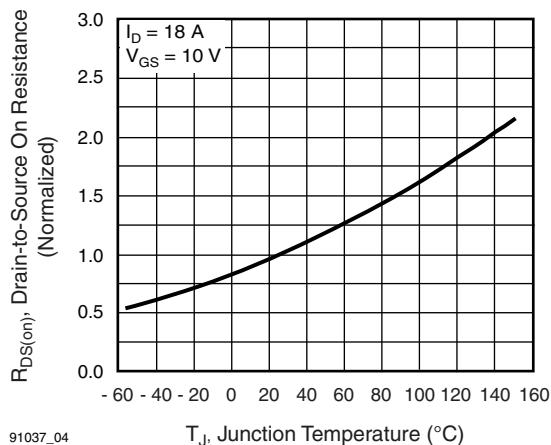


Fig. 4 - Normalized On-Resistance vs. Temperature

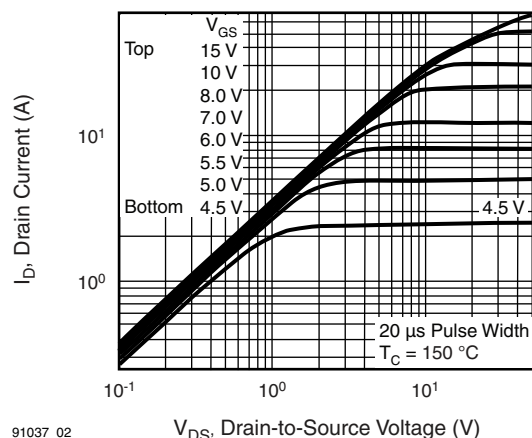


Fig. 2 - Typical Output Characteristics,  $T_J = 175$  °C

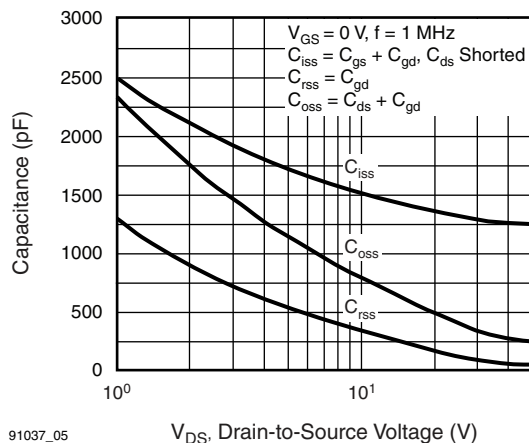


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

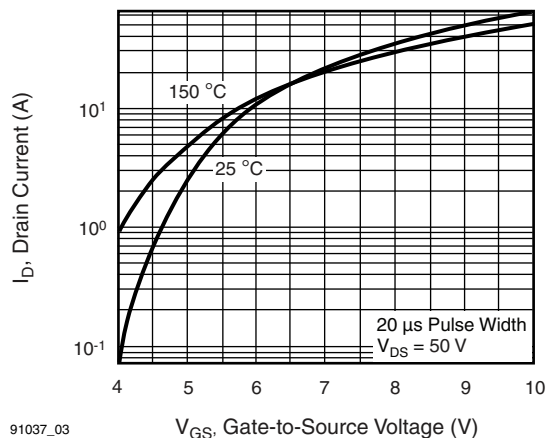


Fig. 3 - Typical Transfer Characteristics

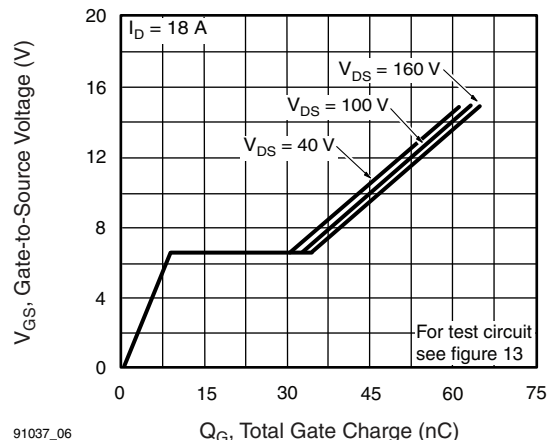
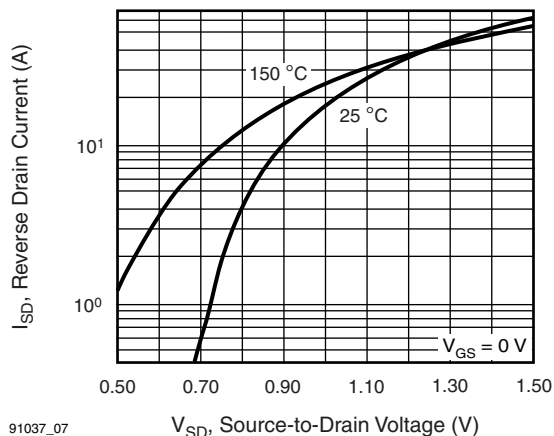
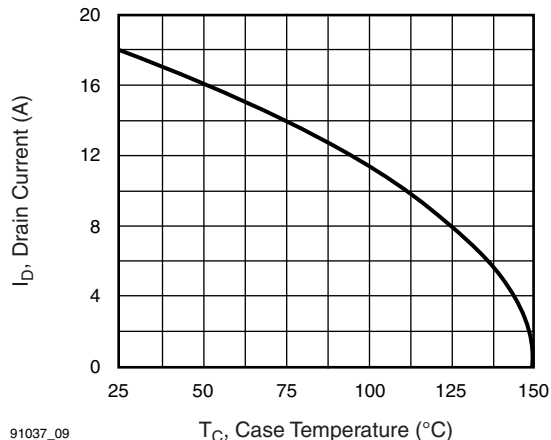
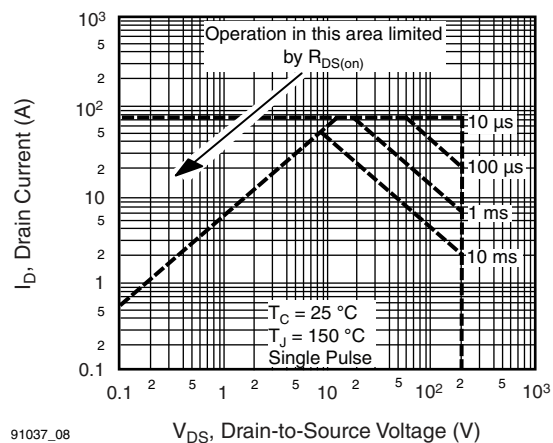
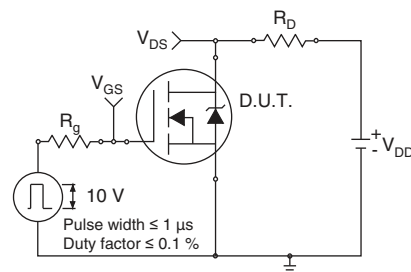
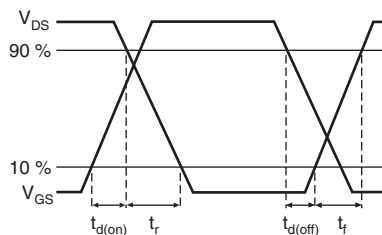
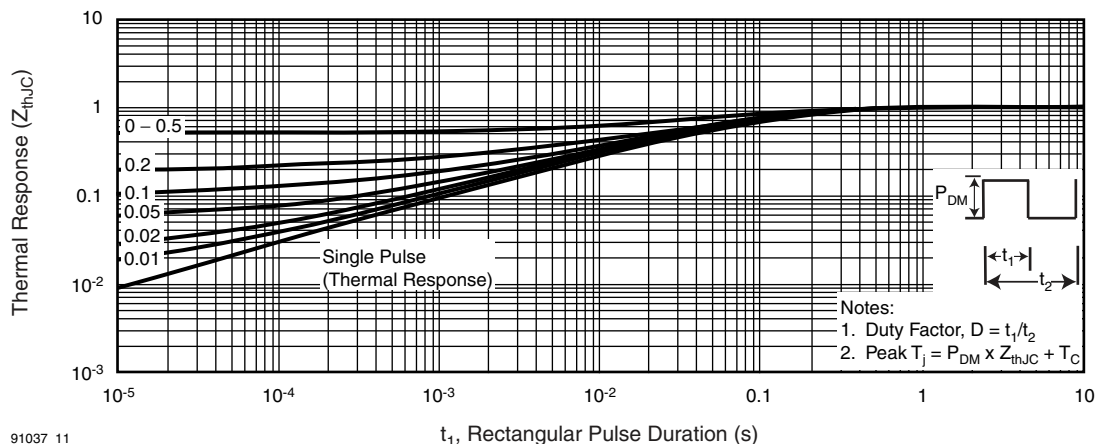
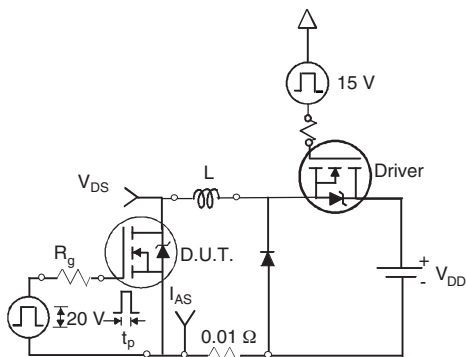
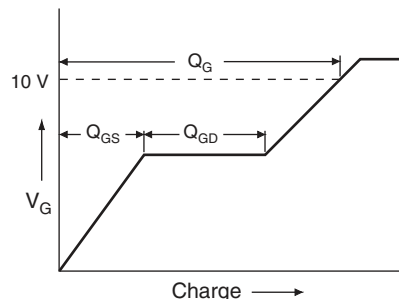
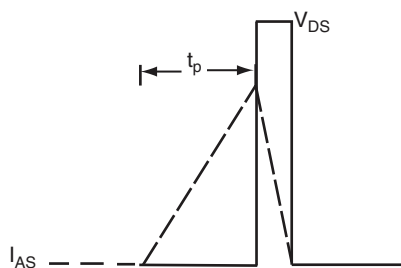
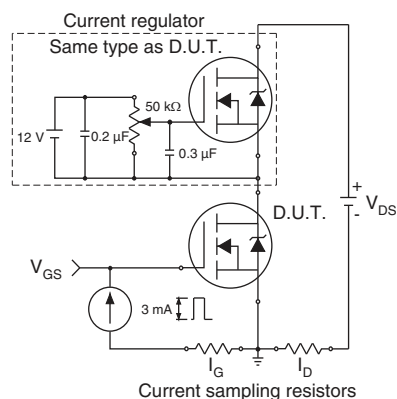
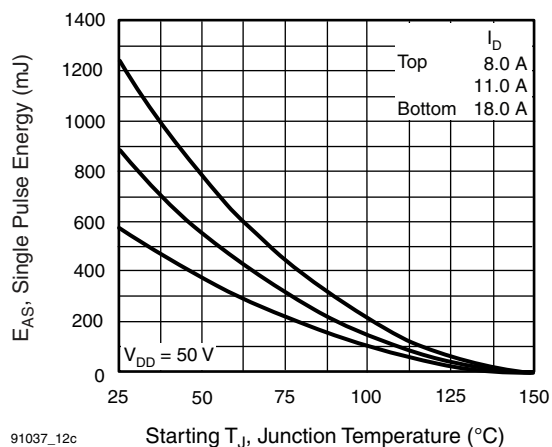
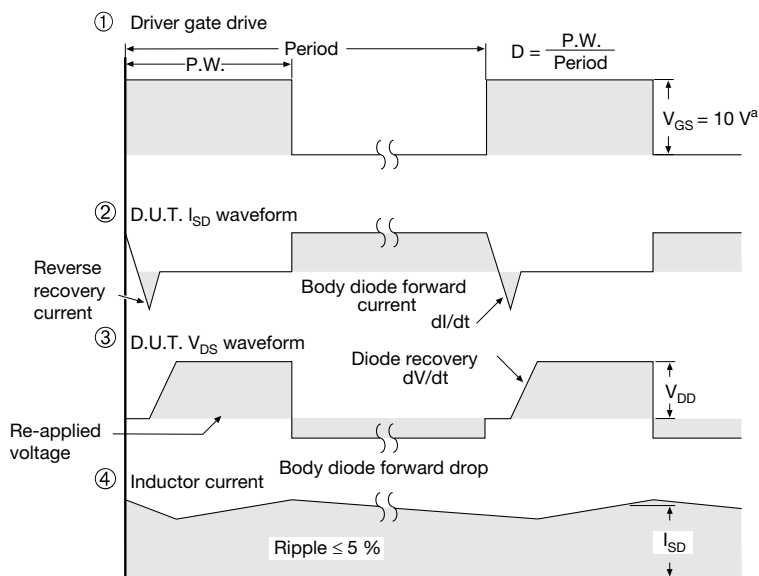
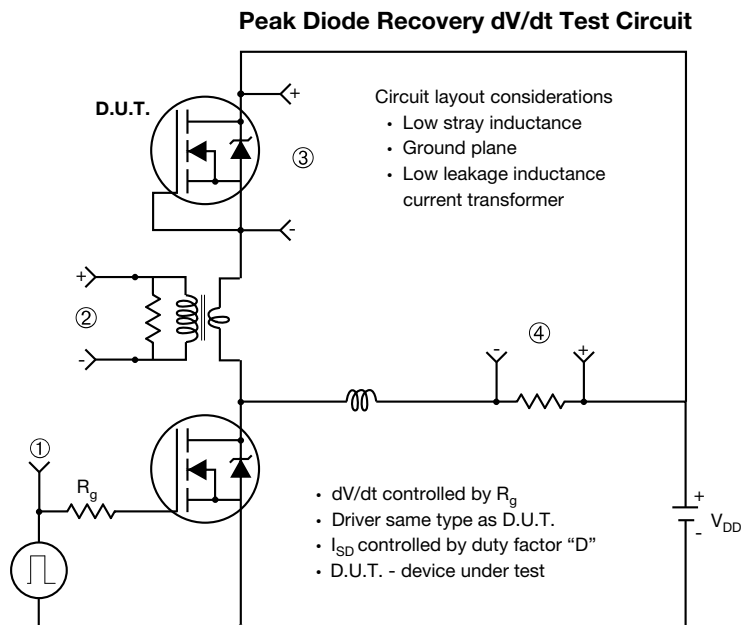


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage


**Fig. 7 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Maximum Safe Operating Area**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**

**Fig. 10 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**


**Fig. 12a - Unclamped Inductive Test Circuit**

**Fig. 13a - Basic Gate Charge Waveform**

**Fig. 12b - Unclamped Inductive Waveforms**

**Fig. 13b - Gate Charge Test Circuit**

**Fig. 12c - Maximum Avalanche Energy vs. Drain Current**


**Note**

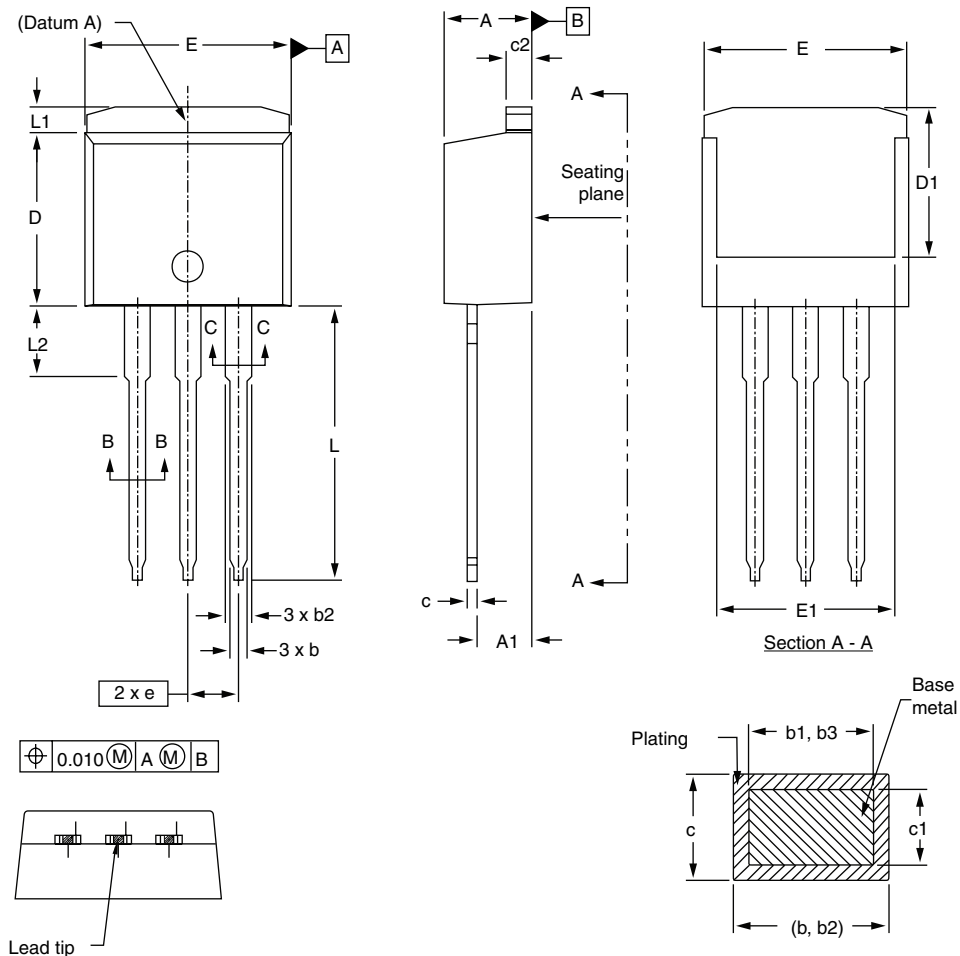
a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?91037>.

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

## I<sup>2</sup>PAK (TO-262) (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08  
DWG: 5977

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.





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